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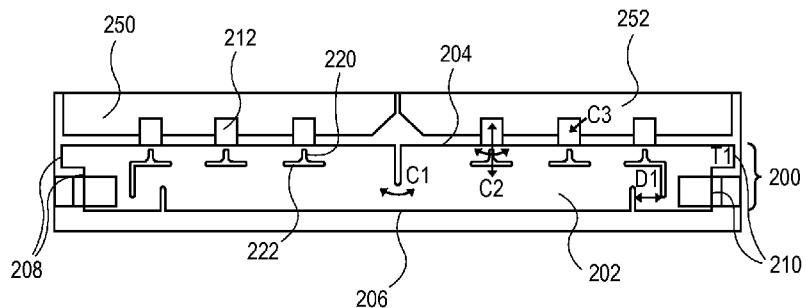
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**(54) Title:** INTERCONNECT FOR AN OPTOELECTRONIC DEVICE



**FIG. 2**

**(57) Abstract:** Interconnects for optoelectronic devices are described. An interconnect may include a stress relief feature. An interconnect may include an L-shaped feature.

## Interconnect for an Optoelectronic Device

### TECHNICAL FIELD

**[0001]** Embodiments of the present invention are in the field of renewable energy and, in particular, interconnects for optoelectronic devices.

### BACKGROUND

**[0002]** Light-emitting diode (LED) and photovoltaic (PV) devices are two common types of optoelectronic devices. Thermal management and assembly of optoelectronic systems, such as systems including LED and PV devices, may be considered when evaluating such systems for fabrication and deployment. For example, the area of systems of devices with cell interconnects is one area ripe for improvements in thermal management, stress management, and assembly. Challenges for the fabrication and deployment of such systems include a possible need for a low resistance thermal path in the interconnect, as well as a flexible accommodation of cells coupled to the interconnect.

### BRIEF DESCRIPTION OF THE DRAWINGS

**[0003]** Figure 1A illustrates a cross-sectional view of a laminated photovoltaic system, in accordance with an embodiment of the present invention.

**[0004]** Figure 1B illustrates a plan view of a laminated photovoltaic system, in accordance with an embodiment of the present invention.

**[0005]** Figure 2 illustrates a plan view of an interconnect for an optoelectronic device, in accordance with an embodiment of the present invention.

**[0006]** Figure 3 illustrates a cross-sectional view of an interconnect for an optoelectronic device highlighting a vertical jog, in accordance with an embodiment of the present invention.

**[0007]** Figure 4 illustrates an isometric view of an interconnect for an optoelectronic device highlighting a solder preform, in accordance with an embodiment of the present invention.

**[0008]** Figure 5 illustrates an isometric view of a portion of an optoelectronic system with an internal bypass diode, in accordance with an embodiment of the present invention.

**[0009]** Figure 6 illustrates a coupling interconnect that can be split to provide a pair of terminal interconnects, in accordance with an embodiment of the present invention.

## DETAILED DESCRIPTION

**[0010]** Interconnects for optoelectronic devices are described herein. In the following description, numerous specific details are set forth, such as specific arrangements of stress relief features in interconnects, in order to provide a thorough understanding of embodiments of the present invention. It will be apparent to one skilled in the art that embodiments of the present invention may be practiced without these specific details. In other instances, well-known fabrication techniques, such as lamination techniques, are not described in detail in order to not unnecessarily obscure embodiments of the present invention. Furthermore, it is to be understood that the various embodiments shown in the Figures are illustrative representations and are not necessarily drawn to scale.

**[0011]** Disclosed herein are interconnects for optoelectronic devices. In one embodiment, an interconnect for an optoelectronic device includes an interconnect body including an inner surface, an outer surface, a first end, and a second end. The interconnect also includes a plurality of bond pads coupled to the inner surface of the interconnect body, between the first and second ends. The interconnect also includes a stress relief feature formed in the interconnect body, the stress relief feature having a plurality of T-shaped slots, each T-shaped slot approximately aligned with a corresponding one of the plurality of bond pads, the vertical portion of each T-shaped slot proximate to the corresponding one of the plurality of bond pads, and the horizontal portion of each T-shaped slot distal from the corresponding one of the plurality of bond pads.

**[0012]** In one embodiment, an interconnect for an optoelectronic device includes an inner surface, an outer surface, a first end, and a second end. The interconnect also includes a plurality of bond pads coupled to the inner surface of the interconnect body, between the first and second ends. The interconnect also includes a feature formed in the interconnect body, the feature having a first L-shaped extension at the first end of the interconnect body and a second L-shaped extension at the second end of the interconnect body, the horizontal bases of each of the first and

second L-shaped extensions proximate to the inner surface and distal from the outer surface of the interconnect body.

**[0013]** In accordance with an embodiment of the present invention, an interconnect with one or more stress relief or L-shaped features is used to improve the reliability of a photovoltaic system and to allow for reduced stress levels in cell solder joints, cell interconnects, and in-laminate bypass diodes. In one embodiment, stress levels in components that are bonded to the interconnect and encapsulated within a photovoltaic laminate are reduced. In an embodiment, designs for interconnects described herein are improved over conventional interconnect designs, since the new designs account for the large coefficient of thermal expansion and rapid increase in stiffness of an encapsulant exposed to low temperature.

**[0014]** In an embodiment, the stress relief features designed into the interconnect address all components that are attached to the interconnect. For example, a series of different structures integrated within a cell interconnect may be used to reduce stress where each component is attached as well as to reduce stresses that would develop along a series of interconnects. In one embodiment, the stress relief features are designed to allow freedom of motion in the directions the components will be strained due to large temperature excursions of an associated photovoltaic system.

**[0015]** Encapsulants may typically be expected to reduce stress in a photovoltaic (PV) laminate due to their low modulus of elasticity. However, in accordance with an embodiment of the present invention, at extremely low temperatures near outdoor extremes or in unheated airplane storage cells, the encapsulant can approach its glass transition temperature. At the glass transition temperature, the modulus can increase by three orders of magnitude. At this point, the encapsulant becomes a stress driver within the package as it also has a very large thermal expansion coefficient. Thus, in an embodiment, stress relief features are utilized and designed to reduce the effects of an encapsulant that is becoming stiff and contracting due to low temperatures.

**[0016]** A common challenge related to reliable operation of laminated photovoltaic systems can be the minimization of thermal stress that develops during temperature excursions. An example of such a laminated photovoltaic system is provided in Figures 1A and 1B, in accordance with an embodiment of the present invention.

**[0017]** Referring to Figure 1A, in a cross-sectional view, and to Figure 1B, in a plan view, a typical laminated solar cell package 100 includes an array of semiconductor solar cells 102 joined by metal interconnects 104 that are encapsulated within a polymer layer 106 between a glass superstrate 108 and a flexible polymer backsheet 110. In order to improve system performance, a bypass diode 112 between cell interconnects 104 as well as a heat sink 114 (via a thermal adhesive 116) may also be integrated, as shown in Figures 1A and 1B. Laminated solar cell packages also contemplated herein are solar cell packages such as those described in U.S. patent application 12/844,594 assigned to SunPower Corporation, entitled “Optoelectronic Device with Bypass Diode,” filed on July 27, 2010, the entire contents of which are hereby incorporated by reference herein.

**[0018]** Typically, a photovoltaic designer may focus on the thermal expansion mismatch of the glass, copper interconnects and silicon cells as the primary stress driver during thermal excursions, relying on the soft polymer encapsulant as a stress relieving feature. However, in an embodiment, at extremely cold temperatures the encapsulant often approaches its glass transition temperature and the stiffness modulus may increase by over two orders of magnitude. In addition to the rapid change in stiffness, the polymer encapsulant may have a relatively high thermal expansion coefficient several times larger than glass and metals. During these conditions, the typically soft encapsulant may become a major stress driver in the package.

**[0019]** Extremely cold temperatures are often realized overnight in outdoor environments as well as during transport in unheated airplane storage cells. In accordance with an embodiment of the present invention, for initial qualification and increased reliability, it is thus crucial that interconnect designs are capable of reducing stress on the components coupled together, e.g., primarily the bypass diodes and cells. In addition to thermal stress, there may also be a need to maximize the thermal coupling between the bypass diode and a heat sink mounted to the back of a laminated package in order to prevent thermal failure of the diode when operating in bypass mode.

**[0020]** In an aspect of the present invention, stress induced by an encapsulant at low temperatures and all intermediate ranges is reduced by incorporating several stress relief features at each interlinked component, as well as by extending additional heat spreading surfaces to regions below a heat sink in close proximity to a diode

attachment point. For example, Figure 2 illustrates a plan view of an interconnect for an optoelectronic device, in accordance with an embodiment of the present invention.

**[0021]** Referring to Figure 2, an interconnect 200 includes an interconnect body 202 having an inner surface 204, an outer surface 206, a first end 208, and a second end 210. A plurality of bond pads 212 is coupled to the inner surface 204 of the interconnect body 202, between the first and second ends 208 and 210, respectively. In an embodiment, one or more stress relief features are formed in the interconnect body 202, as described in more detail below.

**[0022]** In accordance with an embodiment of the present invention, referring again to Figure 2, the stress relief feature of interconnect 200 is a narrow slot C1 positioned in a location approximately equally between the first and second ends 208 and 210, respectively. The narrow slot C1 includes an opening at the inner surface 204 of the interconnect body 202 and extending into the interconnect body 202, but not through to the outer surface 206.

**[0023]** In one embodiment, feature C1 is a narrow slot cut into the center of the interconnect 200 that allows the bending of the interconnect at its mid-plane as needed if two cells (e.g., cells 250 and 252 partially depicted in Figure 2) to which it is rigidly connected rotate to form an effective V-shape (see arrow below C1 in Figure 2). Such rotation may be common given the periodic placement of interconnects down a linear array of cells, as depicted in Figure 1B. In one embodiment, the length of C1 is determined based on the expected displacement of the cells and the maximum allowable stress in the interconnects and bond pads coupled to the cells. In a specific embodiment, feature C1 is typically around 7 millimeters for a 12 millimeter wide interconnect. However, if the length of C1 is too long, it may restrict electrical current flow and add excessive Ohmic losses. In one embodiment, the width of C1 is determined based on the manufacturing tolerances associated with punching or stamping operations as well as the need to reduce stress at the tip of the narrow slot. In a specific embodiment, a typical width for feature C1 is approximately in the range of 0.5 – 1 millimeters, and the tip is a fully rounded semicircle to reduce stress concentrations. A small width may also limit the length of an Ohmic bottleneck, which may conduct the full photocurrent of a string of cells.

**[0024]** In accordance with an embodiment of the present invention, referring again to Figure 2, the stress relief feature of interconnect 200 is a plurality of T-shaped slots C2, each T-shaped slot C2 approximately aligned with a corresponding one of

the plurality of bond pads 212. The vertical portion 220 of each T-shaped slot C2 is proximate to the corresponding one of the plurality of bond pads 212, and the horizontal portion 222 of each T-shaped slot C2 is distal from the corresponding one of the plurality of bond pads 212.

**[0025]** In one embodiment, feature C2 is a T-shaped slot in the interconnect 200 that allows both rotation and normal displacement of the interconnect 200 relative to a cell (e.g., cell 250 or 252). At extremely cold temperatures, an encapsulant may approach its glass transition temperature and, due to its high thermal expansion coefficient, act as a stress driver. Surprisingly, in this condition, the encapsulant may pull an interconnect closer to a cell. In one embodiment, feature C2 thus allows for a small deformation of the interconnect 200 towards a cell to relax strain in the encapsulant, limiting the stress at the cell-interconnect bond. In a specific embodiment, each of the three connections to a cell (e.g., the three connections on the right side of interconnect 200 made to cell 252) contributes approximately one-third of the cumulative photocurrent being conducted in the string. Between and below these connections, the current may flow substantially in the wider portion of the interconnect 200 below the C2 features. As such, in a particular embodiment, the  $I^2R$  losses associated with such features are low.

**[0026]** In accordance with an embodiment of the present invention, referring again to Figure 2, the stress relief feature of interconnect 200 is a vertical jog C3 near to or at the location where one of the plurality of bond pads 212 is coupled to the inner surface of the interconnect body 202. Figure 3 illustrates a cross-sectional view of an interconnect for an optoelectronic device highlighting a vertical jog, in accordance with an embodiment of the present invention.

**[0027]** Referring to Figure 3, in one embodiment, feature C3 is a vertical jog in the interconnect 200 that creates an out-of-plane mechanical coupling that reduces stress when the interconnect 200 is pulled closer to a cell (e.g., cell 252) by an encapsulant 390. In addition, in a specific embodiment, the thinner region not only further reduces the stress between the cell 252 and interconnect 200 but also reduces vertical height differential between a heat sink 392, cell 252, and interconnect 200, reducing thermal resistance from the cell 252 and an associated diode to ambient.

**[0028]** Furthermore, in an embodiment, referring to Figure 4, solder 499 can be added to the cell bond pads 212 of the interconnect 200. In one embodiment, by preprocessing a solder pad onto the interconnect 200, the stringing or

wiring of an array of cells can be performed at a much higher throughput and with a much tighter process control than by dispensing solder paste during cell-to-interconnect soldering.

In accordance with an embodiment of the present invention, referring again to Figure 2, the stress relief feature of interconnect 200 is a combination of slots D1. D1 includes a first narrow slot in a location proximate to the second end 210 and distal from the first end 208 of interconnect 200. The first narrow slot includes an opening at the outer surface 206 of the interconnect body 202 and extending into the interconnect body 202, but not through to the inner surface 204. D1 also includes a second narrow slot between the first narrow slot and the second end 210. The second narrow slot is between and orthogonal to the inner and outer surfaces 204 and 206, respectively, but does not open into either of the inner and outer surfaces 204 and 206. Furthermore, the second narrow slot is coupled to the horizontal portion of an outermost T-shaped slot C2 of the plurality of T-shaped slots, as depicted in Figure 2.

**[0029]** In one embodiment, feature D1 is specifically designed to allow the ends 208 and 210 of the interconnect 200 to extend or retract to reduce stress on a diode package and to reduce any long-range stresses that might develop down an entire length of an array of cells. In a specific embodiment, feature D1 includes both the straight slot from the outside edge 206 of the interconnect 200 and the additional slot added to the T-shaped slot C2 at each bond pad 212. In a specific embodiment, feature D1 also allows expansion of the joints between a diode and interconnect 200 during the soldering or bonding assembly operations. If a soldering step is used to attach the diodes without feature D1, stress may increase as the components cool down from the soldering temperature. In a particular embodiment, for a long string of several interconnects and diodes, such stress is otherwise appreciable and would otherwise result in early failure of the diodes during lamination as well as in displacement of the cells from nominal positions.

**[0030]** In one embodiment, in the standard operating mode of the cells, feature D1 has a minimal electrical impact on the circuit as there is nearly zero electrical current flowing through the diode. The cell connections are oriented such that the outermost regions (left and right ends) of the interconnect 200 conduct approximately one-third of the cumulative photocurrent generated by the cells. As a result, in an embodiment, the  $I^2R$  losses near feature D1 are substantially less than they would be if this feature were placed closer to the center of the interconnect 200 where a higher

current always flows even when the diode is not in bypass mode. When the diodes are in bypass mode, the full string photocurrent may flow through and around feature D1. Thus, in an embodiment, D1 becomes a larger source of electrical losses. However, these losses are small compared to the power dissipation otherwise within the diode in bypass mode.

**[0031]** In accordance with an embodiment of the present invention, referring again to Figure 2, interconnect 200 includes a feature T1 formed in the interconnect body 202. The feature T1 includes a first L-shaped extension at the first end 208 of the interconnect body 202, and a second L-shaped extension at the second end 210 of the interconnect body 202. The horizontal bases of each of the first and second L-shaped extensions are proximate to the inner surface 204 and distal from the outer surface 206 of the interconnect body 202.

**[0032]** In one embodiment, feature T1 is designed to increase thermal coupling between a diode and a heat sink that extends partially over the interconnect 202. For example, Figure 5 illustrates an isometric view of a portion of an optoelectronic system with an internal bypass diode, in accordance with an embodiment of the present invention.

**[0033]** Referring to Figure 5, in one embodiment, the L-shaped extension (or pair of extensions) to the interconnect 200 allows additional heat sink 392 fin coupling in close proximity to a diode (e.g., a cell 500 bypass diode) 502, thus reducing the thermal gradient to ambient for a diode operating in bypass mode. In a specific embodiment, the reduced temperature of the diode 502 also helps reduce any thermal stress that would develop due to an otherwise localized hot spot. In an embodiment, the L-shaped extension is an extended area for increased thermal coupling between an interconnect and a heat sink mounted to an optoelectronic system.

**[0034]** It is to be understood that different combinations, or even solo use of, one or more of the above features and stress relief features may be included in an interconnect. For example, in an embodiment, an interconnect for an optoelectronic device includes an interconnect body including an inner surface, an outer surface, a first end, and a second end. A plurality of bond pads is coupled to the inner surface of the interconnect body, between the first and second ends. A stress relief feature is formed in the interconnect body. The stress relief feature includes a plurality of T-shaped slots, each T-shaped slot approximately aligned with a corresponding one of

the plurality of bond pads, the vertical portion of each T-shaped slot proximate to the corresponding one of the plurality of bond pads, and the horizontal portion of each T-shaped slot distal from the corresponding one of the plurality of bond pads.

**[0035]** In another embodiment, an interconnect for an optoelectronic device includes an interconnect body having an inner surface, an outer surface, a first end, and a second end. A plurality of bond pads is coupled to the inner surface of the interconnect body, between the first and second ends. A feature is formed in the interconnect body, the feature having a first L-shaped extension at the first end of the interconnect body and a second L-shaped extension at the second end of the interconnect body. The horizontal bases of each of the first and second L-shaped extensions are proximate to the inner surface and distal from the outer surface of the interconnect body.

**[0036]** In another embodiment, an interconnect for an optoelectronic device includes an interconnect body having an inner surface, an outer surface, a first end, and a second end. A plurality of bond pads is coupled to the inner surface of the interconnect body, between the first and second ends. A stress relief feature is formed in the interconnect body, the stress relief feature having a plurality of T-shaped slots, each T-shaped slot approximately aligned with a corresponding one of the plurality of bond pads. The vertical portion of each T-shaped slot is proximate to the corresponding one of the plurality of bond pads. The horizontal portion of each T-shaped slot is distal from the corresponding one of the plurality of bond pads. The interconnect also includes a first L-shaped extension at the first end of the interconnect body. A second L-shaped extension is at the second end of the interconnect body. The horizontal bases of each of the first and second L-shaped extensions are proximate to the inner surface and distal from the outer surface of the interconnect body.

**[0037]** In one embodiment, the stress relief feature further includes a first narrow slot in a location approximately equally between the first and second ends. The first narrow slot has an opening at the inner surface of the interconnect body and extends into the interconnect body, but not through to the outer surface. The stress relief feature further includes a second narrow slot in a location proximate to the first end and distal from the second end. The second narrow slot has an opening at the outer surface of the interconnect body and extends into the interconnect body, but not through to the inner surface. The stress relief feature further includes a third narrow

slot between the second narrow slot and the first end. The third narrow slot is between and orthogonal to the inner and outer surfaces, but does not open into either of the inner and outer surfaces. Also, the third narrow slot is coupled to the horizontal portion of an outer-most T-shaped slot of the plurality of T-shaped slots. The stress relief feature further includes a vertical jog near to or at the location where one of the plurality of bond pads is coupled to the inner surface of the interconnect body.

**[0038]** In accordance with an embodiment of the present invention, an interconnect contemplated herein is a coupling interconnect. The coupling interconnect may be used to couple two optoelectronic cells, as described above in association with Figures 2, 4 and 5. However, in another embodiment, the interconnect is a terminal interconnect. For example, Figure 6 illustrates a coupling interconnect that can be split to provide a pair of terminal interconnects, in accordance with an embodiment of the present invention.

**[0039]** Referring to Figure 6, a coupling interconnect 600 includes a first half 602 and a second, symmetrical half 604 joined at a location 606 with the first half 602. Coupling interconnect 600 includes stress relief features 608 and other features described above, such as L-shaped features 610. Coupling interconnect 600 may be split along axis 612 to provide two terminal interconnects.

**[0040]** In association with the discussion of Figures 2-4 and 6 above, a plurality of interconnects, such as interconnect 200 or 600, may be included in an optoelectronic system. Thus, in accordance with an embodiment of the present invention, an optoelectronic system includes a plurality of pairs of optoelectronic devices. In one embodiment, each optoelectronic device is a back-contact solar cell. The optoelectronic system also includes a plurality of bypass diodes, one or more of the bypass diodes disposed between each of the pairs of optoelectronic devices. The optoelectronic system also includes a plurality of heat spreader units, one or more of the heat spreader units disposed above, and extending over, each of the bypass diodes. The optoelectronic system also includes a plurality of heat sinks, one or more of the heat sinks disposed above each of the heat spreader units. In an embodiment, the optoelectronic system, interconnects or pairs of interconnects are disposed between pairs of optoelectronic devices, such as pairs of solar cells. In one embodiment, one or more of the interconnects has one or more of a stress relief feature and an L-shaped feature, such as the stress relief features and L-shaped features described above in association with interconnects 200 and 600.

**[0041]** In accordance with an embodiment of the present invention, a method of fabricating an interconnect for an optoelectronic device includes forming an interconnect body having an inner surface, an outer surface, a first end, a second end, and a plurality of bond pads coupled to the inner surface of the interconnect body, between the first and second ends. The method further includes forming one or more stress relief features and L-shaped features in the interconnect body, such as the stress relief features and L-shaped features described above in association with interconnects 200 and 600.

**[0042]** Thus, interconnects for optoelectronic devices have been disclosed. In accordance with an embodiment of the present invention, an interconnect for an optoelectronic device includes a stress relief feature. In one embodiment, the interconnect includes an interconnect body having an inner surface, an outer surface, a first end, and a second end. A plurality of bond pads is coupled to the inner surface of the interconnect body, between the first and second ends. A stress relief feature is formed in the interconnect body. The stress relief feature includes a plurality of T-shaped slots, each T-shaped slot approximately aligned with a corresponding one of the plurality of bond pads, the vertical portion of each T-shaped slot proximate to the corresponding one of the plurality of bond pads, and the horizontal portion of each T-shaped slot distal from the corresponding one of the plurality of bond pads. In accordance with another embodiment of the present invention, an interconnect for an optoelectronic device includes an L-shaped feature. In one embodiment, an interconnect includes an interconnect body having an inner surface, an outer surface, a first end, and a second end. A plurality of bond pads is coupled to the inner surface of the interconnect body, between the first and second ends. A feature is formed in the interconnect body, the feature having a first L-shaped extension at the first end of the interconnect body and a second L-shaped extension at the second end of the interconnect body. The horizontal bases of each of the first and second L-shaped extensions are proximate to the inner surface and distal from the outer surface of the interconnect body.

## CLAIMS

What is claimed is:

1. An interconnect for an optoelectronic device, the interconnect comprising:
  - an interconnect body comprising an inner surface, an outer surface, a first end, and a second end;
  - a plurality of bond pads coupled to the inner surface of the interconnect body, between the first and second ends; and
  - a stress relief feature formed in the interconnect body, the stress relief feature comprising a plurality of T-shaped slots, each T-shaped slot approximately aligned with a corresponding one of the plurality of bond pads, the vertical portion of each T-shaped slot proximate to the corresponding one of the plurality of bond pads, and the horizontal portion of each T-shaped slot distal from the corresponding one of the plurality of bond pads.
2. The interconnect of claim 1, wherein the stress relief feature further comprises a narrow slot in a location approximately equally between the first and second ends, the narrow slot comprising an opening at the inner surface of the interconnect body and extending into the interconnect body, but not through to the outer surface.
3. The interconnect of claim 1, wherein the stress relief feature further comprises a first narrow slot in a location proximate to the first end and distal from the second end, the first narrow slot comprising an opening at the outer surface of the interconnect body and extending into the interconnect body, but not through to the inner surface, and a second narrow slot between the first narrow slot and the first end, the second narrow slot between and orthogonal to the inner and outer surfaces, but not opening into either of the inner and outer surfaces, and the second narrow slot coupled to the horizontal portion of an outer-most T-shaped slot of the plurality of T-shaped slots.
4. The interconnect of claim 1, wherein the stress relief feature further comprises a vertical jog near to or at the location where one of the plurality of bond pads is coupled to the inner surface of the interconnect body.

5. The interconnect of claim 1, wherein the stress relief further feature comprises:
  - a first narrow slot in a location approximately equally between the first and second ends, the first narrow slot comprising an opening at the inner surface of the interconnect body and extending into the interconnect body, but not through to the outer surface;
  - a second narrow slot in a location proximate to the first end and distal from the second end, the second narrow slot comprising an opening at the outer surface of the interconnect body and extending into the interconnect body, but not through to the inner surface;
  - a third narrow slot between the second narrow slot and the first end, the third narrow slot between and orthogonal to the inner and outer surfaces, but not opening into either of the inner and outer surfaces, and the third narrow slot coupled to the horizontal portion of an outer-most T-shaped slot of the plurality of T-shaped slots; and
- a vertical jog near to or at the location where one of the plurality of bond pads is coupled to the inner surface of the interconnect body.
6. The interconnect of claim 1, wherein the interconnect is a coupling interconnect.
7. The interconnect of claim 1, wherein the interconnect is a terminal interconnect.
8. An interconnect for an optoelectronic device, the interconnect comprising:
  - an interconnect body comprising an inner surface, an outer surface, a first end, and a second end;
  - a plurality of bond pads coupled to the inner surface of the interconnect body, between the first and second ends; and
  - a feature formed in the interconnect body, the feature comprising a first L-shaped extension at the first end of the interconnect body and a second L-shaped extension at the second end of the interconnect body, the horizontal bases of each of the first and second L-shaped extensions proximate to the inner surface and distal from the outer surface of the interconnect body.
9. The interconnect of claim 8, further comprising:

a stress relief feature comprising a narrow slot in a location approximately equally between the first and second ends, the narrow slot comprising an opening at the inner surface of the interconnect body and extending into the interconnect body, but not through to the outer surface.

10. The interconnect of claim 8, further comprising:

a stress relief feature further comprising a vertical jog near to or at the location where one of the plurality of bond pads is coupled to the inner surface of the interconnect body.

11. The interconnect of claim 8, further comprising a stress relief feature, the stress relief feature comprising:

a narrow slot in a location approximately equally between the first and second ends, the narrow slot comprising an opening at the inner surface of the interconnect body and extending into the interconnect body, but not through to the outer surface; and

a vertical jog near to or at the location where one of the plurality of bond pads is coupled to the inner surface of the interconnect body.

12. The interconnect of claim 8, wherein the interconnect is a coupling interconnect.

13. The interconnect of claim 8, wherein the interconnect is a terminal interconnect.

14. An interconnect for an optoelectronic device, the interconnect comprising:

an interconnect body comprising an inner surface, an outer surface, a first end, and a second end;

a plurality of bond pads coupled to the inner surface of the interconnect body, between the first and second ends;

a stress relief feature formed in the interconnect body, the stress relief feature comprising a plurality of T-shaped slots, each T-shaped slot approximately aligned with a corresponding one of the plurality of bond pads, the vertical portion of each T-shaped slot proximate to the corresponding one of the plurality of bond pads, and the horizontal portion of each T-shaped slot distal from the corresponding one of the plurality of bond pads;

a first L-shaped extension at the first end of the interconnect body; and  
a second L-shaped extension at the second end of the interconnect body, the  
horizontal bases of each of the first and second L-shaped extensions proximate  
to the inner surface and distal from the outer surface of the interconnect body.

15. The interconnect of claim 14, wherein the stress relief feature further comprises a narrow slot in a location approximately equally between the first and second ends, the narrow slot comprising an opening at the inner surface of the interconnect body and extending into the interconnect body, but not through to the outer surface.

16. The interconnect of claim 14, wherein the stress relief feature further comprises a first narrow slot in a location proximate to the first end and distal from the second end, the first narrow slot comprising an opening at the outer surface of the interconnect body and extending into the interconnect body, but not through to the inner surface, and a second narrow slot between the first narrow slot and the first end, the second narrow slot between and orthogonal to the inner and outer surfaces, but not opening into either of the inner and outer surfaces, and the second narrow slot coupled to the horizontal portion of an outer-most T-shaped slot of the plurality of T-shaped slots.

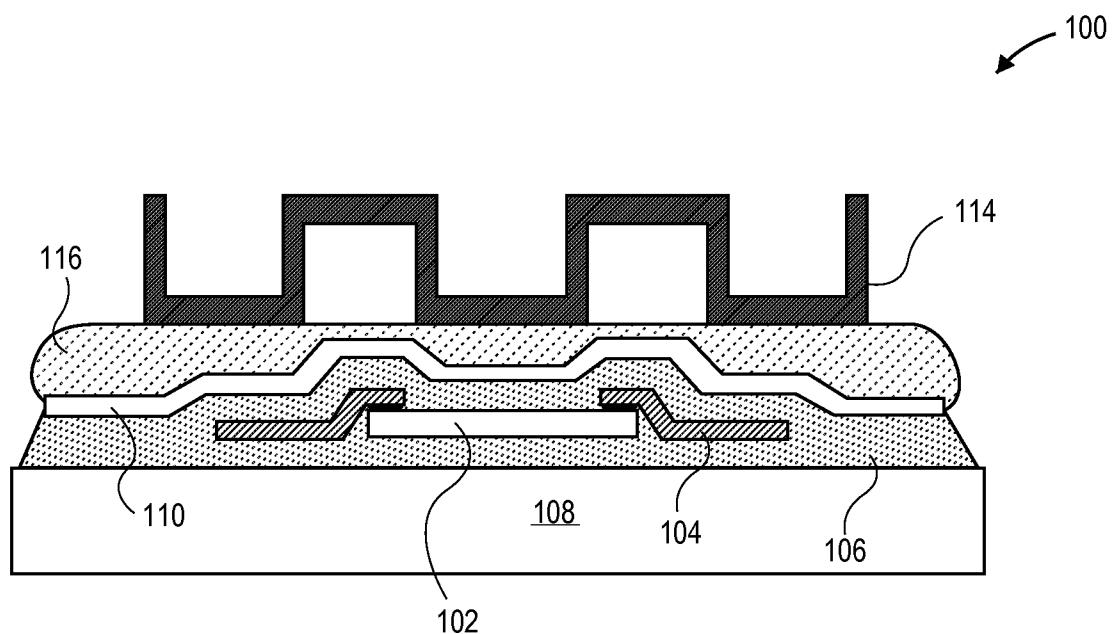
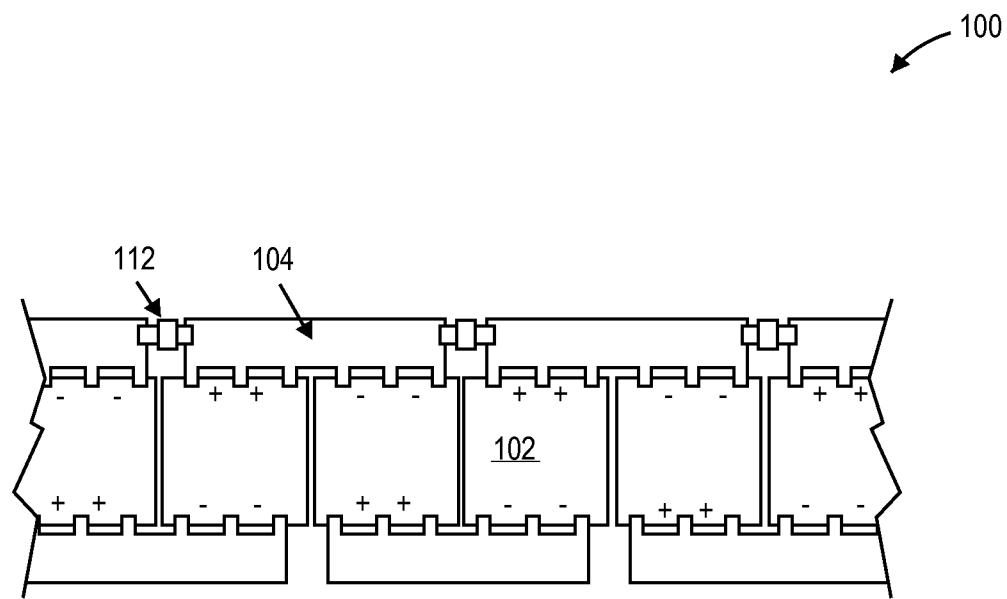
17. The interconnect of claim 14, wherein the stress relief feature further comprises a vertical jog near to or at the location where one of the plurality of bond pads is coupled to the inner surface of the interconnect body.

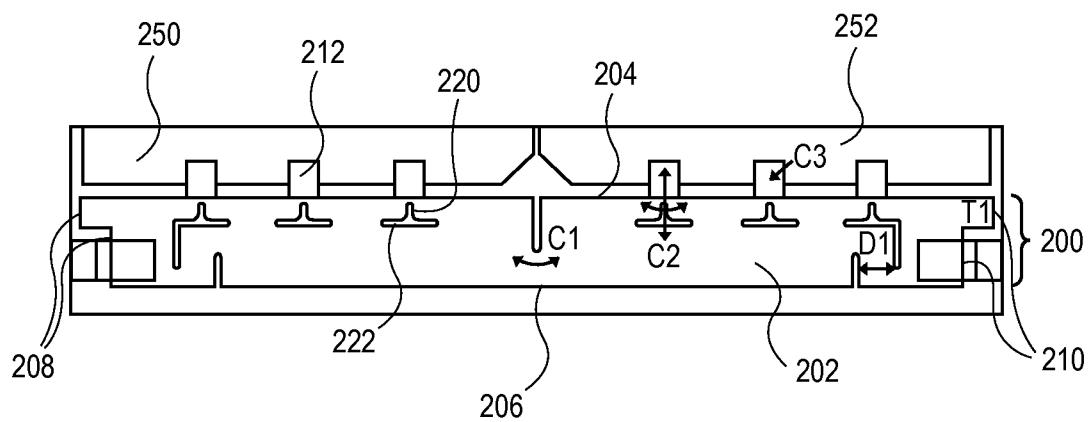
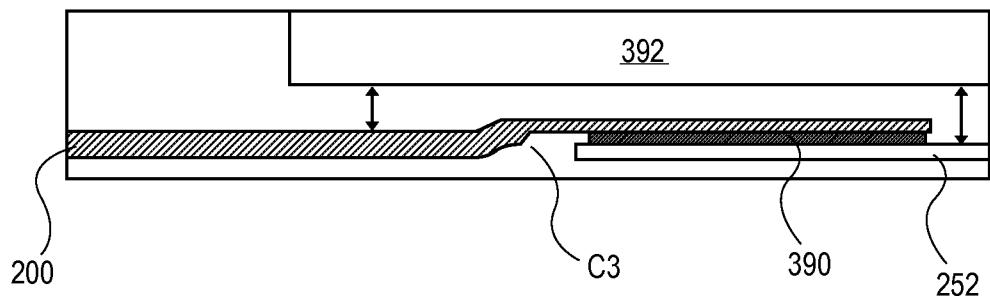
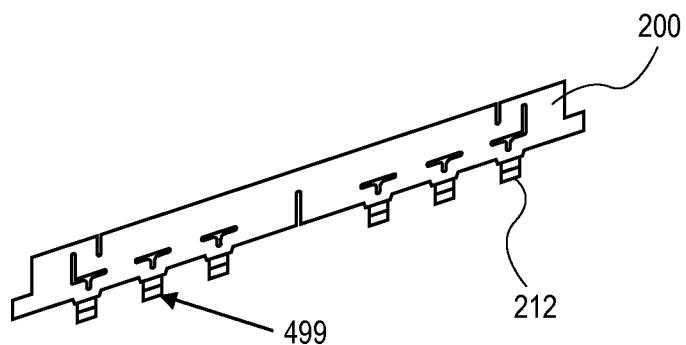
18. The interconnect of claim 14, wherein the stress relief feature further comprises:  
a first narrow slot in a location approximately equally between the first and second ends, the first narrow slot comprising an opening at the inner surface of the interconnect body and extending into the interconnect body, but not through to the outer surface;  
a second narrow slot in a location proximate to the first end and distal from the second end, the second narrow slot comprising an opening at the outer surface of the interconnect body and extending into the interconnect body, but not through to the inner surface;

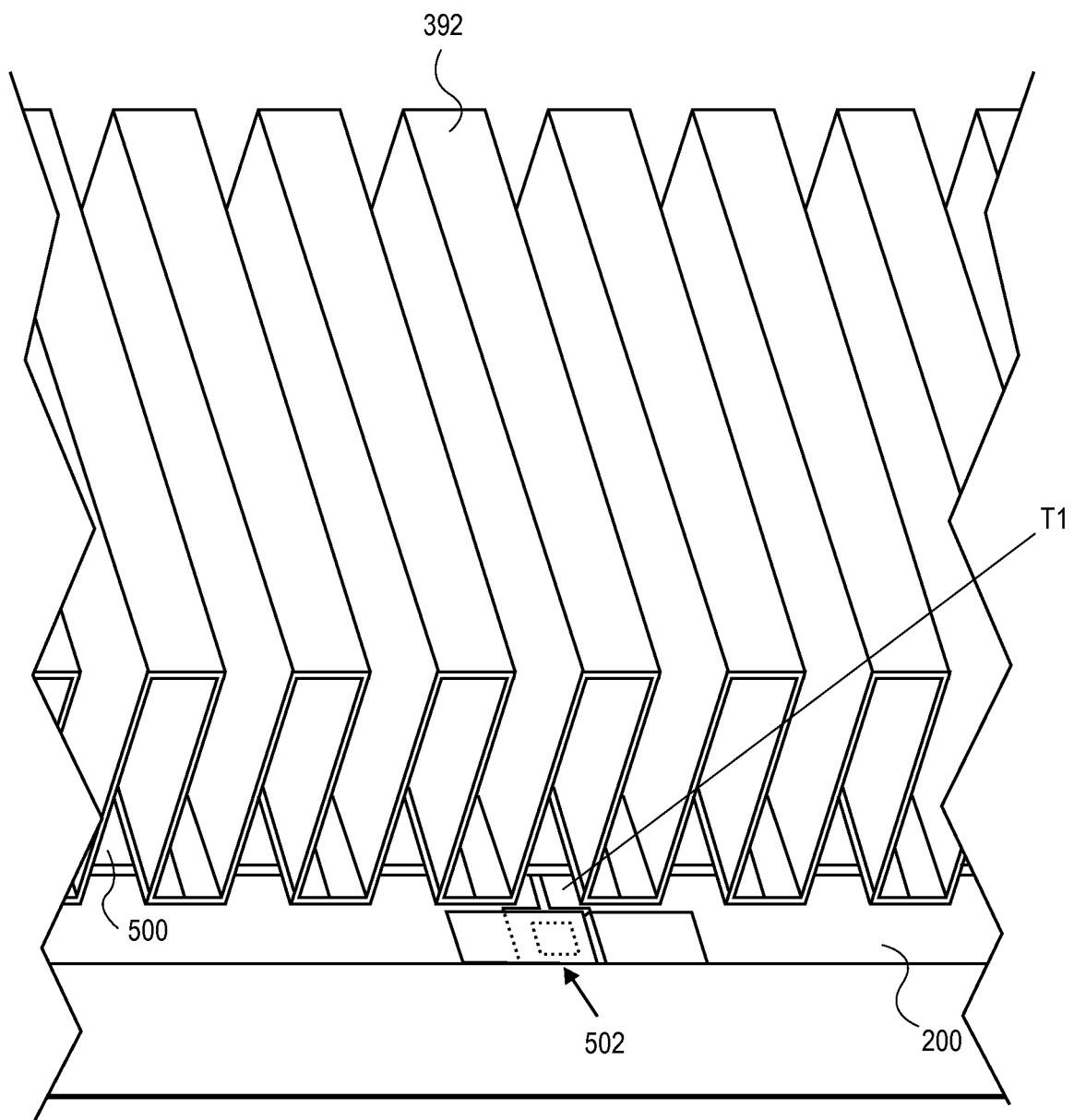
a third narrow slot between the second narrow slot and the first end, the third narrow slot being and orthogonal to the inner and outer surfaces, but not opening into either of the inner and outer surfaces, and the third narrow slot coupled to the horizontal portion of an outer-most T-shaped slot of the plurality of T-shaped slots; and

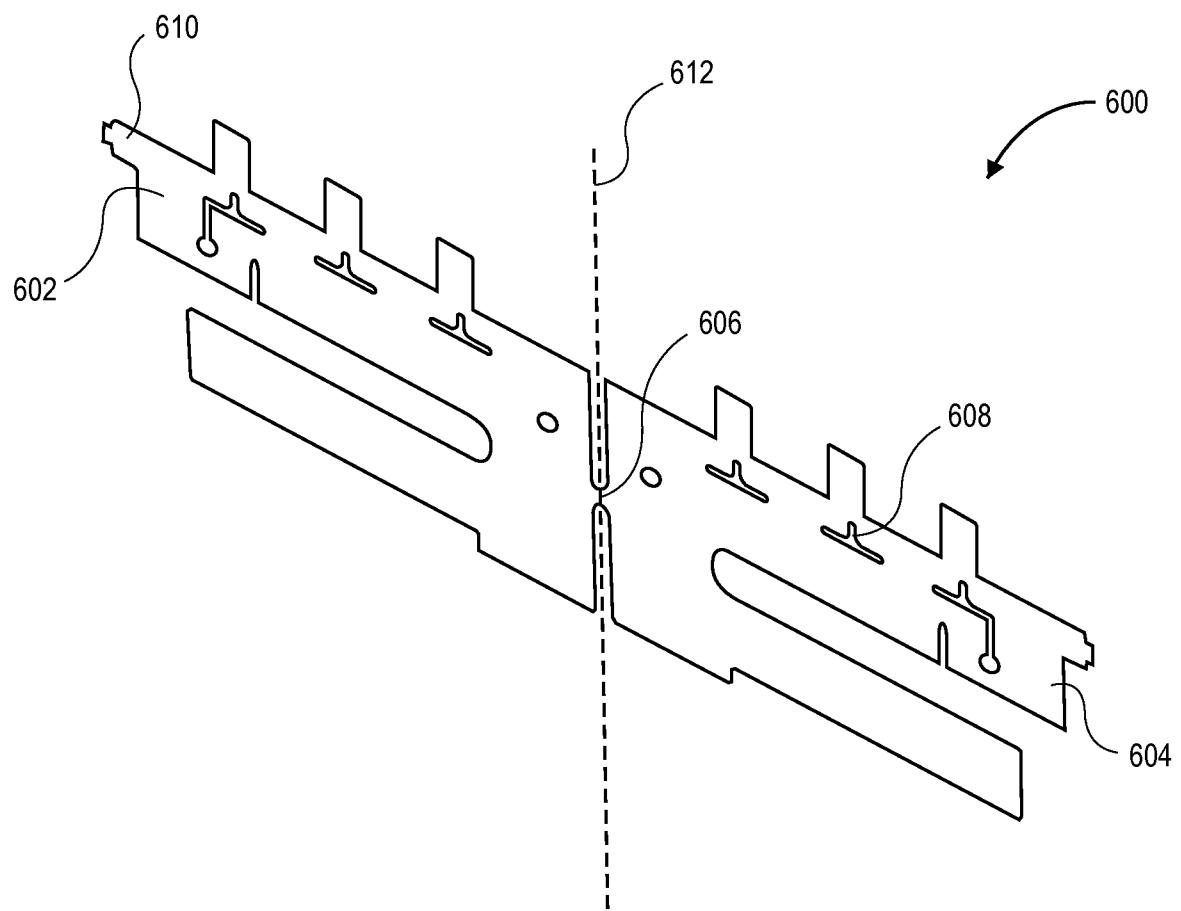
a vertical jog near to or at the location where one of the plurality of bond pads is coupled to the inner surface of the interconnect body.

19. The interconnect of claim 14, wherein the interconnect is a coupling interconnect.
20. The interconnect of claim 14, wherein the interconnect is a terminal interconnect.

**FIG. 1A****FIG. 1B**

**FIG. 2****FIG. 3****FIG. 4**

**FIG. 5**

**FIG. 6**

## INTERNATIONAL SEARCH REPORT

International application No.  
**PCT/US2011/044743****A. CLASSIFICATION OF SUBJECT MATTER****H01L 33/62(2010.01)i, H01L 33/36(2010.01)i, H01L 31/04(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

**B. FIELDS SEARCHED**

Minimum documentation searched (classification system followed by classification symbols)

H01L 33/62; G09F 9/00; H01R 11/11; H01L 31/042; H01L 31/00

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched  
Korean utility models and applications for utility models  
Japanese utility models and applications for utility modelsElectronic data base consulted during the international search (name of data base and, where practicable, search terms used)  
eKOMPASS(KIPO internal) & Keywords: interconnect, strain, solar, photovoltaic, relief, bond pad, slot.**C. DOCUMENTS CONSIDERED TO BE RELEVANT**

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 2010-0144218 A1 (ROSE DOUGLAS H. et al.) 10 June 2010 See abstract; claims 1-20; figures 1-12.	1-20
A	KR 10-0469141 B1 (Rohm Co., Ltd.) 08 June 2005 See abstract; claims 1-17; figures 1-24.	1-20
A	JP 10-335686 A (FUJI ELECTRIC CORP RES & DEV LTD) 18 December 1998 See abstract; claims 1-9; figures 1-8.	1-20
A	US 2005-0268959 A1 (PETER ASCHENBRENNER et al.) 08 December 2005 See abstract; claims 1-20; figures 1-8.	1-20

 Further documents are listed in the continuation of Box C. See patent family annex.

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Date of the actual completion of the international search  
28 FEBRUARY 2012 (28.02.2012)

Date of mailing of the international search report

**02 MARCH 2012 (02.03.2012)**

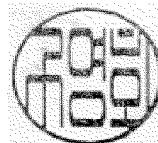
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**INTERNATIONAL SEARCH REPORT**

Information on patent family members

International application No.

**PCT/US2011/044743**

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